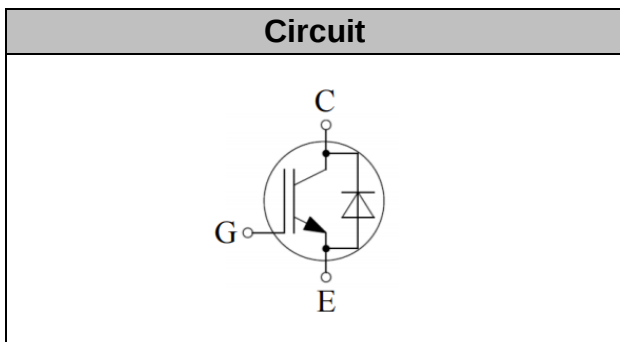


IGBT Discrete

V_{CE}	650	V
I_C	10	A
$V_{CE(SAT)} I_C=10A$	1.40	V



Applications

- Soft switching applications
- Air conditioning
- Motor drive inverter

Features

- High speed smooth switching device for hard & soft switching
- Maximum junction temperature 175°C
- Positive temperature coefficient
- High ruggedness, temperature stable

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-Emitter Breakdown Voltage	V_{CE}	650	V
DC Collector Current, limited by T_{jmax} $T_C=25^{\circ}C$ $T_C=100^{\circ}C$	I_C	20 10	A
Diode Forward Current, limited by T_{jmax} $T_C=25^{\circ}C$ $T_C=100^{\circ}C$	I_F	20 10	A
Continuous Gate-Emitter Voltage	V_{GE}	± 20	V
Transient Gate-Emitter Voltage ($t_p \leq 10\mu s, D < 0.010$)	V_{GE}	± 30	V
Turn off Safe Operating Area $V_{CE} \leq 600V$, $T_j \leq 150^{\circ}C$		40	A
Pulsed Collector Current, $V_{GE}=15V$, t_p limited by T_{jmax}	I_{CM}	40	A
Short Circuit Withstand Time, $V_{GE}=15V$, $V_{CE} \leq 400V$	T_{SC}	5	μs
Diode Pulsed Current, t_p limited by T_{jmax}	I_{Fpuls}	40	A
Power Dissipation, $T_j=175^{\circ}C, T_C=25^{\circ}C$	P_{tot}	100	W

Operating Junction Temperature	T_j	-40...+175	°C
Storage Temperature	T_s	-55...+150	°C
Soldering Temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	°C

Electrical Characteristics of the IGBT ($T_j = 25^\circ\text{C}$ unless otherwise specified):

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Collector-Emitter Breakdown Voltage	BV_{CES}	$V_{GE}=0V, I_C=250\mu A$	650		-	V
Gate Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=1mA$	4.4	5.2	6.0	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=10A$ $T_j=25^\circ\text{C}$ $T_j=125^\circ\text{C}$ $T_j=150^\circ\text{C}$		1.40 1.55 1.60	1.70	V
Zero Gate Voltage Collector Current	I_{CES}	$V_{CE}=650V, V_{GE}=0V$ $T_j=25^\circ\text{C}$ $T_j=150^\circ\text{C}$			0.25 1.00	mA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE}=0V, V_{GE}=\pm 20V$			± 200	nA

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic						
Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V,$ $f=1MHz$	-	0.89	-	nF
Output capacitance	C_{oes}		-	0.04	-	
Reverse Transfer Capacitance	C_{res}		-	0.01	-	
Gate Charge	Q_G	$V_{CC}=300V, I_C=10A,$ $V_{GE}=15V$	-	0.059	-	uC
Short circuit collector current	$I_{C(SC)}$	$V_{GE}=15V, t_{SC} \leq 5\mu s$ $V_{CC}=400V,$ $T_{j,start}=25^\circ\text{C}$	-	110	-	A

Electrical Characteristics of the Diode (T_j= 25°C unless otherwise specified):

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Diode Forward Voltage	V _F	I _F = 10A T _j = 25°C, T _j = 125°C T _j = 150°C		1.70 1.50 1.40	2.20	V

Switching Characteristic, Inductive Load

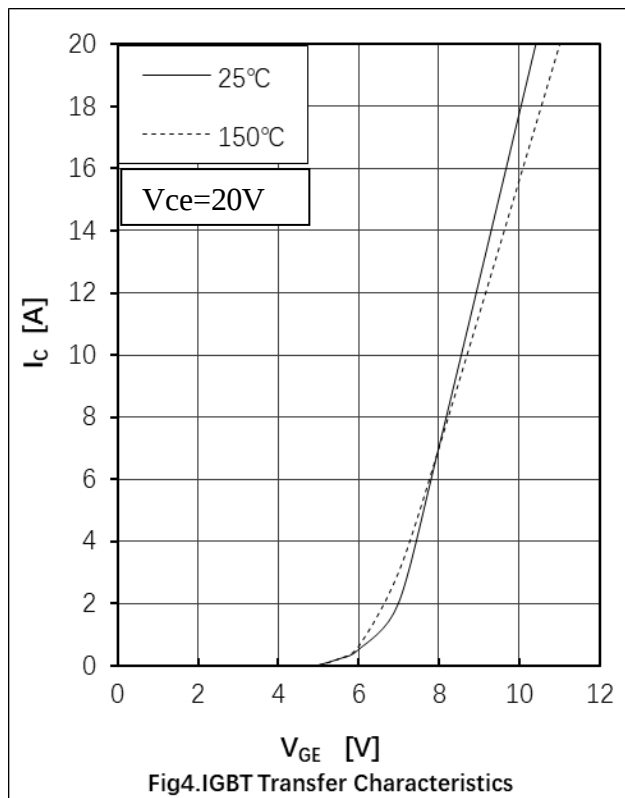
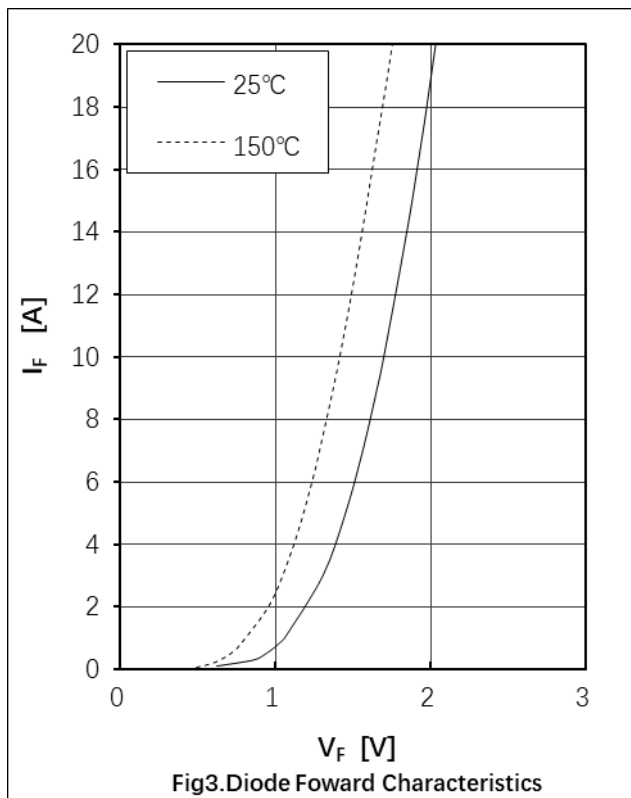
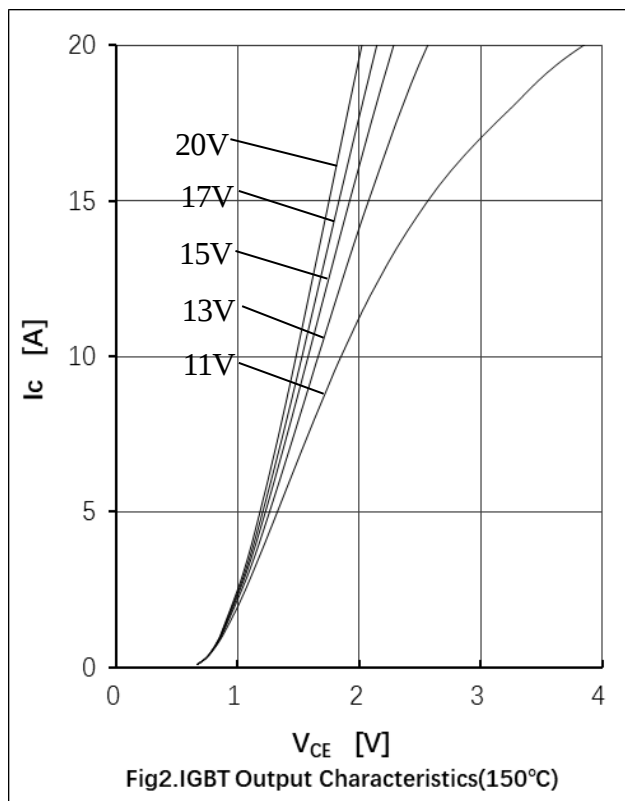
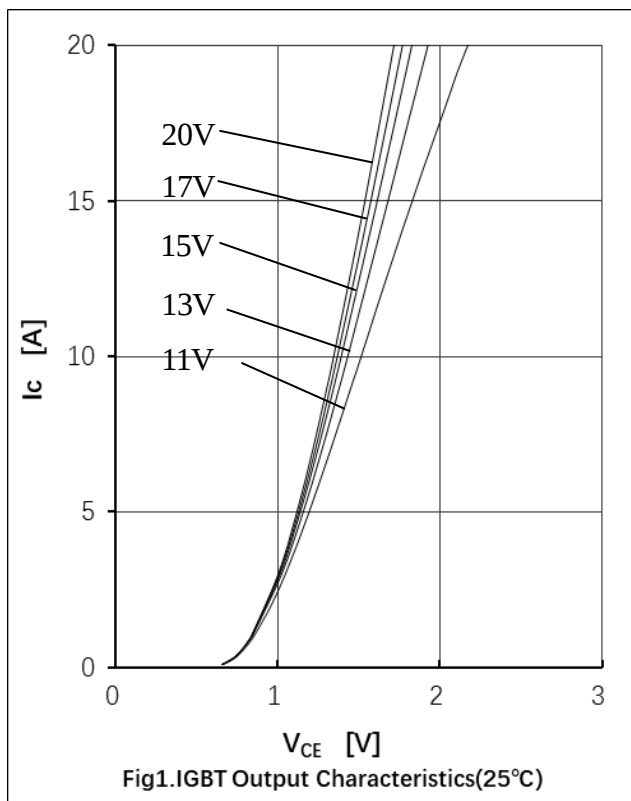
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at T _j = 25℃						
Turn-on Delay Time	t _{d(on)}	T _j =25℃ V _{CC} = 300V, I _C =10A, V _{GE} =-5V~15V, R _g =51 Ω	-	10	-	ns
Rise Time	t _r		-	26	-	ns
Turn-on Energy	E _{on}		-	0.36	-	mJ
Turn-off Delay Time	t _{d(off)}		-	68	-	ns
Fall Time	t _f		-	135	-	ns
Turn-off Energy	E _{off}		-	0.17	-	mJ
Dynamic , at T _j = 125℃						
Turn-on Delay Time	t _{d(on)}	T _j =125℃ V _{CC} = 300V, I _C =10A, V _{GE} =-5V~15V, R _g =51 Ω	-	14	-	ns
Rise Time	t _r		-	35	-	ns
Turn-on Energy	E _{on}		-	0.42	-	mJ
Turn-off Delay Time	t _{d(off)}		-	68	-	ns
Fall Time	t _f		-	162	-	ns
Turn-off Energy	E _{off}		-	0.29	-	mJ
Dynamic , at T _j = 150℃						
Turn-on Delay Time	t _{d(on)}	T _j =150℃ V _{CC} = 300V, I _C =10A, V _{GE} =-5V~15V, R _g =51 Ω	-	16	-	ns
Rise Time	t _r		-	41	-	ns
Turn-on Energy	E _{on}		-	0.46	-	mJ
Turn-off Delay Time	t _{d(off)}		-	69	-	ns
Fall Time	t _f		-	181	-	ns
Turn-off Energy	E _{off}		-	0.33	-	mJ

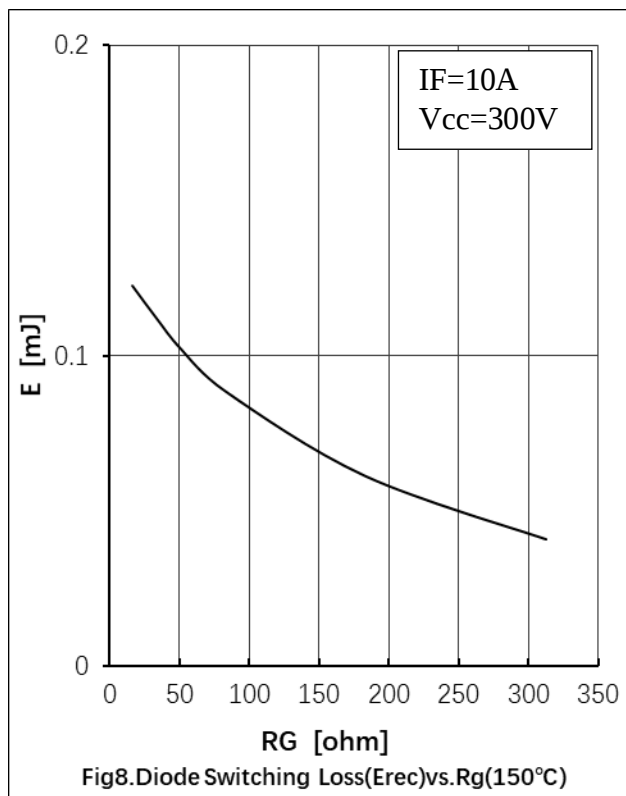
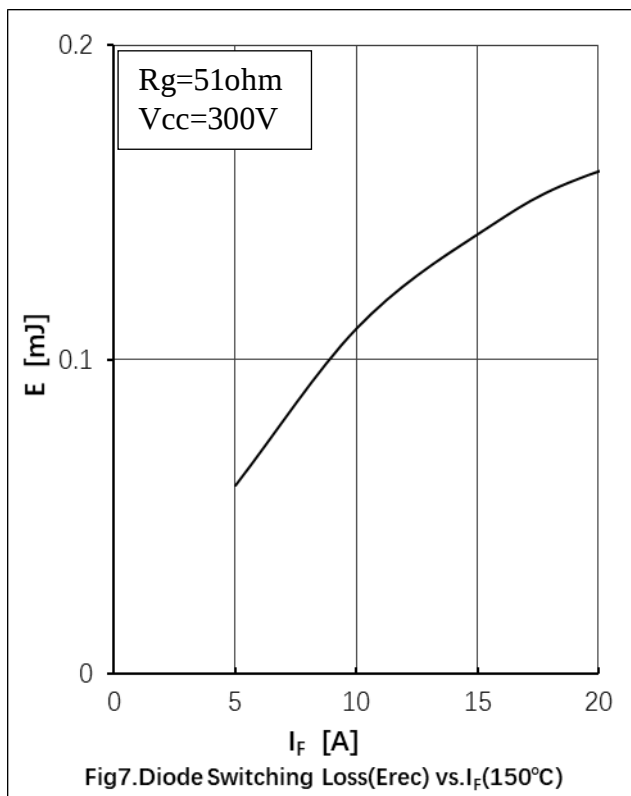
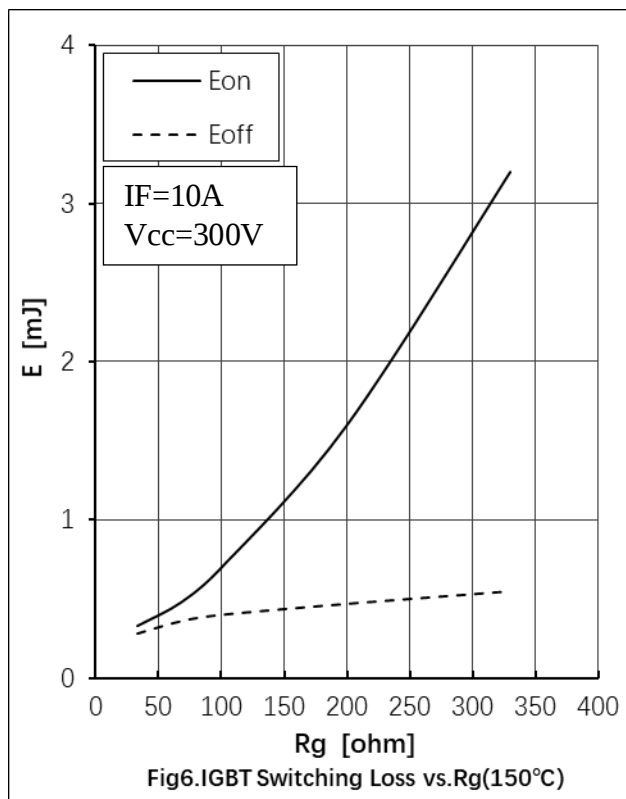
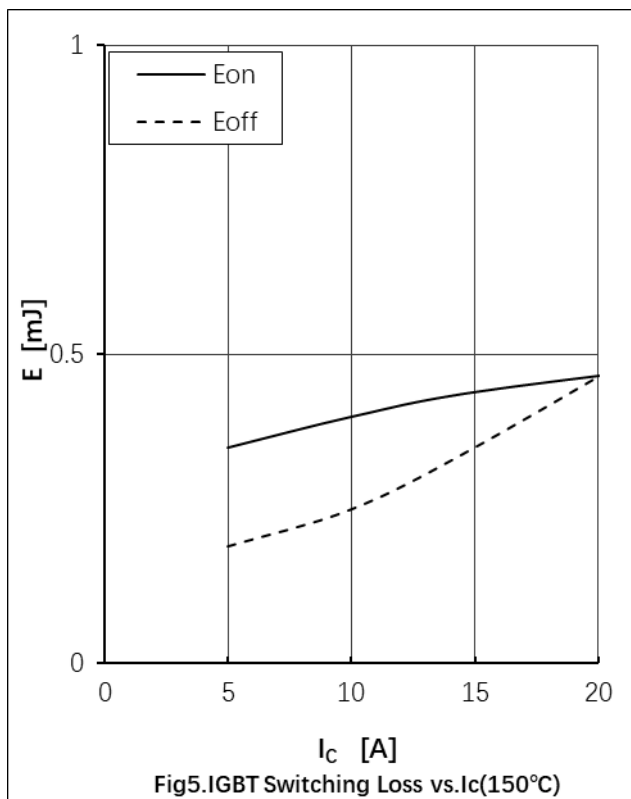
Electrical Characteristics of the DIODE

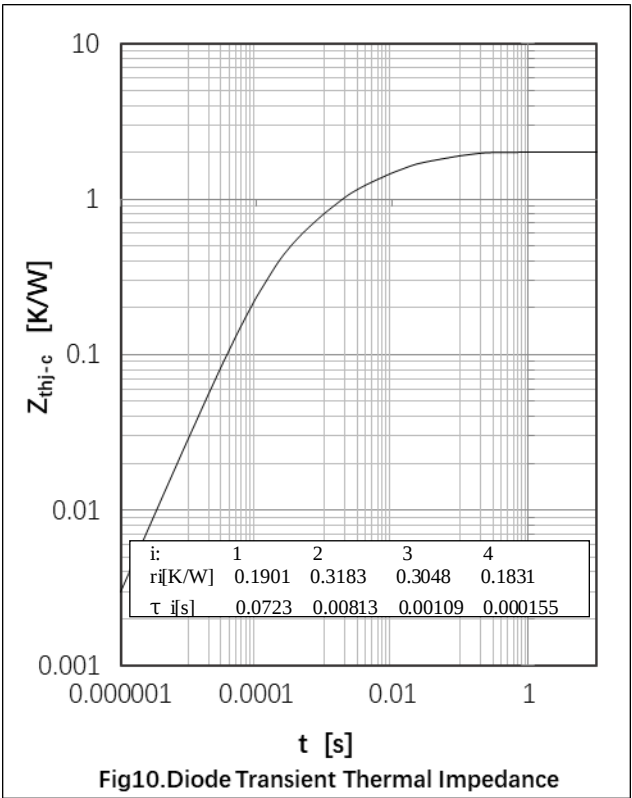
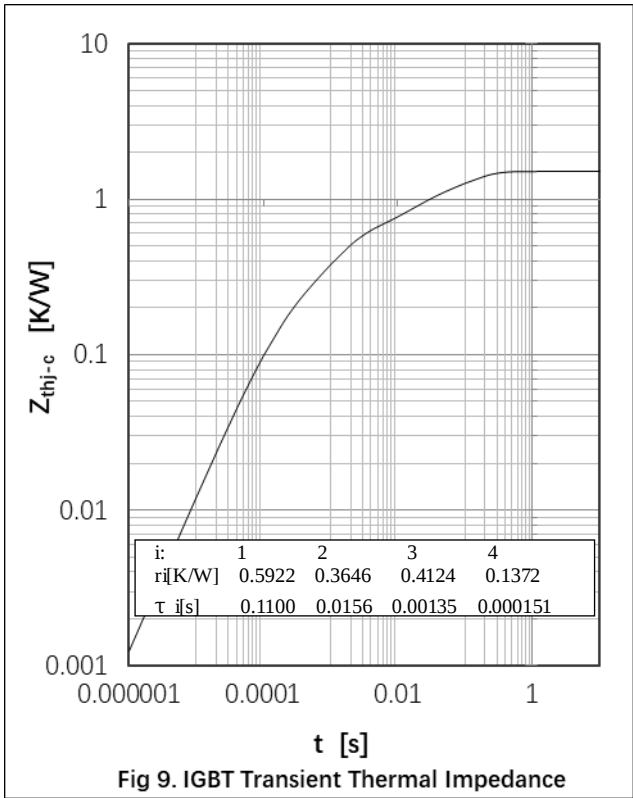
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Dynamic , at Tj= 25°C						
Reverse Recovery Current	I _{rr}	I _F =10A, V _R =300V, -di/dt= 365A/μs,	-	6	-	A
Diode reverse recovery time	trr		-	176	-	ns
Reverse Recovery Charge	Q _{rr}		-	0.12	-	uC
Reverse Recovery Energy	E _{rec}		-	0.05	-	mJ
Dynamic , at Tj= 125°C						
Reverse Recovery Current	I _{rr}	I _F =10A, V _R =300V, -di/dt= 365A/μs,	-	7	-	A
Diode reverse recovery time	trr		-	189	-	ns
Reverse Recovery Charge	Q _{rr}		-	0.48	-	uC
Reverse Recovery Energy	E _{rec}		-	0.09	-	mJ
Dynamic , at Tj= 150°C						
Reverse Recovery Current	I _{rr}	I _F =10A, V _R =300V, -di/dt= 365A/μs,	-	8	-	A
Diode reverse recovery time	trr		-	195	-	ns
Reverse Recovery Charge	Q _{rr}		-	0.62	-	uC
Reverse Recovery Energy	E _{rec}		-	0.11	-	mJ

Thermal Resistance

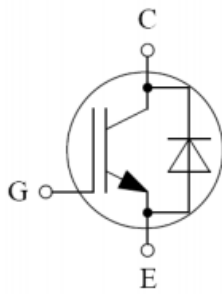
Parameter	Symbol	Max. Value	Unit
IGBT Thermal Resistance, Junction - Case	R _{th(j-c)}	1.5	K/W
Diode Thermal Resistance, Junction - Case	R _{th(j-c)}	2.0	K/W
Thermal Resistance, Junction - Ambient	R _{th(j-a)}	60	K/W





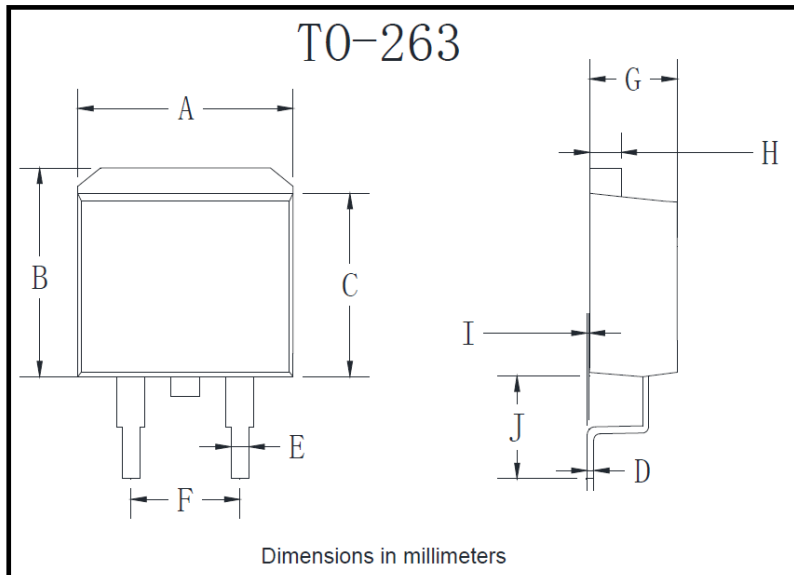


● Circuit Diagram



● Package Outline Information

CASE: TO 263



TO-263		
Dim	Min	Max
A	9.5	11.5
B	9.7	10.5
C	8.4	9.0
D	0.28	0.64
E	0.68	0.94
F	4.55	5.6
G	4.04	5.10
H	1.14	1.4
I	0	0.2
J	4.9	6.05

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